

Abstract

Method and process reactor for sequential gas phase deposition by means of a process chamber and an auxiliary chamber

In a process chamber (10) of a process reactor (1), a sequential gas phase deposition (ALD, atomic layer deposition) of two or more precursors fed in by means of process gases is controlled, the process chamber (10) being connected to an auxiliary chamber (20) for a change of precursor and so the precursor to be removed is rarefied in the process chamber (10), so that a process duration of the sequential gas phase deposition that is determined by a change of precursor is reduced.

(Figure 1)